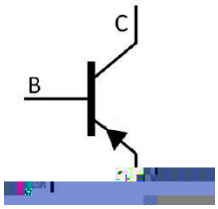
Silicon PNP transistor in a SOT-23 Plastic Package.

Excellent h_{FE} linearity, complementary pair with KTC3876.

General amplifier and switching application.



PIN 1 Base PIN 2 Emitter PIN 3 Collector

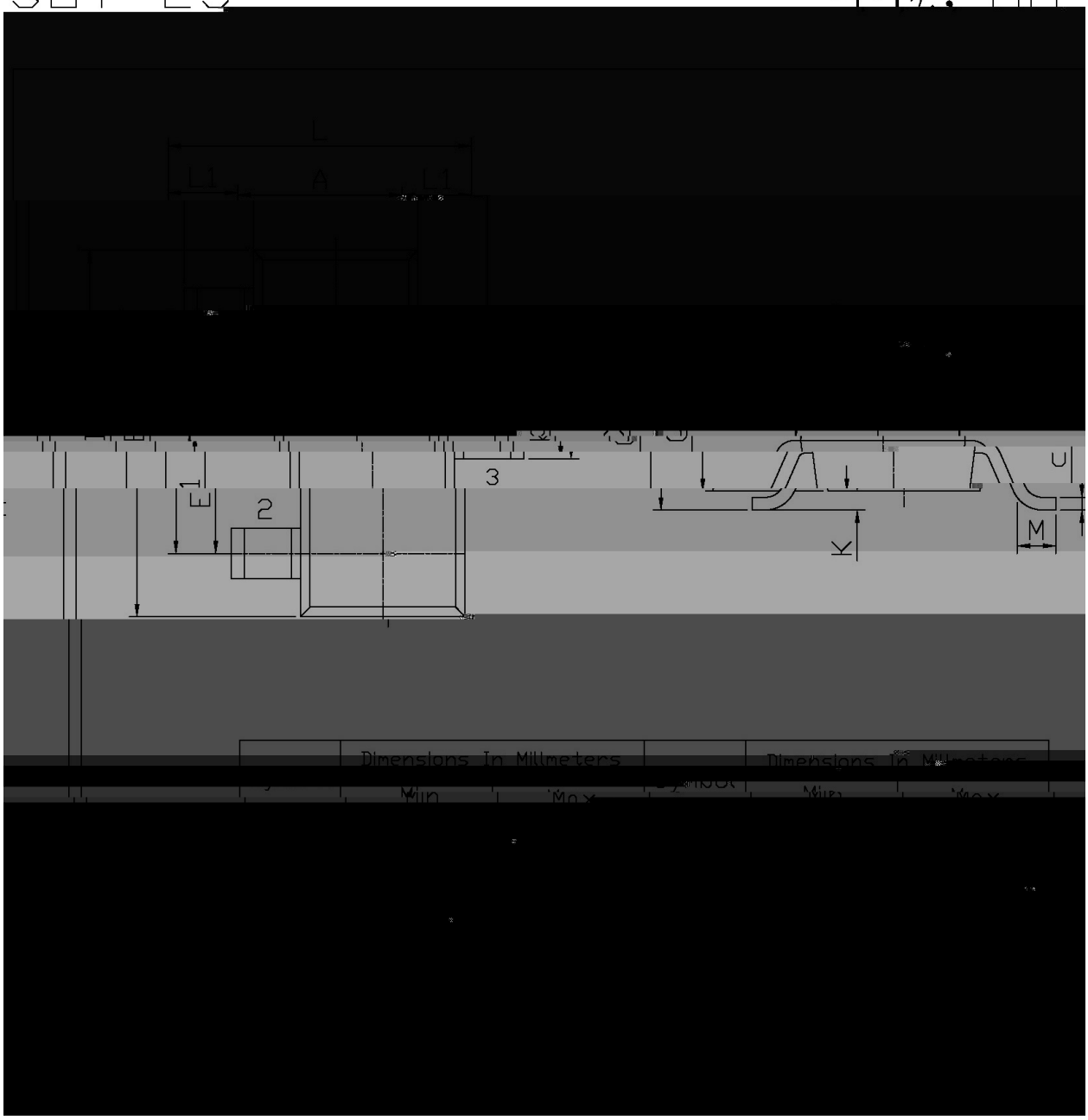
h_{FE} Classifications Symbol	O	Y	GR
h_{FE} Range	70 140	120 240	200 400
Marking	HAZO	HAZY	HAZG

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-500	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-35V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-100mA	70		400	
	$h_{FE(2)}$	V_{CE}=-6.0V I_C=-400mA	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA I_B=-10mA		-0.1	-0.25	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1.0V I_C=-100mA		-0.8	-1.0	V
Transition Frequency	f_T	V_{CE}=-6.0V I_C=-20mA		200		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-6.0V I_E=0 f=1.0MHz		13		pF

-600
COMMON
1k
COMMON EMITTER
Ta=25°C

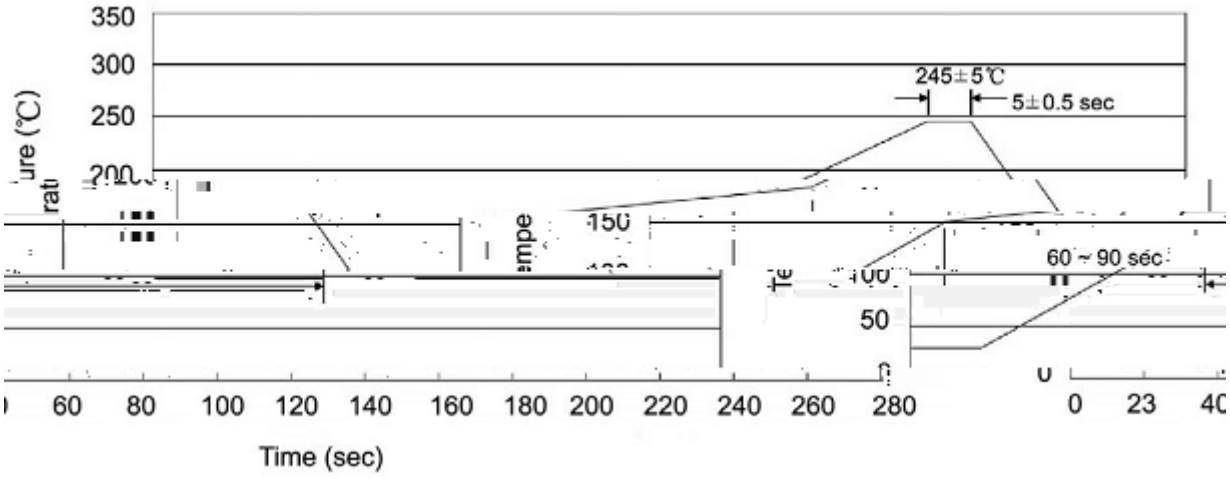
SOT-23 单位：mm



Note:

	Company Code
AZ	Product Type
	h_{FE} Classifications Symbol

Temperature Profile for IR Reflow Soldering(Pb-Free)



		Note:	
1	25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.	
2	245 5 5 0.5sec;	2.Peak Temp.:245 5 , Duration:5 0.5sec.	
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.	

260 5 10 1 sec. Temp.:260 5 Time:10 1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱